

Won Jong Yoo

List of Publications by Year in descending order

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times ranked

12076
citing authors

#	ARTICLE	IF	CITATIONS
1	Flexible and Transparent MoS ₂ Field-Effect Transistors on Hexagonal Boron Nitride-Graphene Heterostructures. ACS Nano, 2013, 7, 7931-7936.	14.6	947
2	High-Performance Perovskite-Graphene Hybrid Photodetector. Advanced Materials, 2015, 27, 41-46.	21.0	753
3	Fermi Level Pinning at Electrical Metal Contacts of Monolayer Molybdenum Dichalcogenides. ACS Nano, 2017, 11, 1588-1596.	14.6	618
4	Controlled charge trapping by molybdenum disulphide and graphene in ultrathin heterostructured memory devices. Nature Communications, 2013, 4, 1624.	12.8	595
5	Lateral MoS ₂ p-n Junction Formed by Chemical Doping for Use in High-Performance Optoelectronics. ACS Nano, 2014, 8, 9332-9340.	14.6	507
6	Highly Stretchable Piezoelectric-Pyroelectric Hybrid Nanogenerator. Advanced Materials, 2014, 26, 765-769.	21.0	469
7	Ultimate thin vertical p-n junction composed of two-dimensional layered molybdenum disulfide. Nature Communications, 2015, 6, 6564.	12.8	285
8	p-Type Polar Transition of Chemically Doped Multilayer MoS ₂ Transistor. Advanced Materials, 2016, 28, 2345-2351.	21.0	197
9	Transferred via contacts as a platform for ideal two-dimensional transistors. Nature Electronics, 2019, 2, 187-194.	26.0	172
10	Modulation of Quantum Tunneling via a Vertical Two-Dimensional Black Phosphorus and Molybdenum Disulfide p-n Junction. ACS Nano, 2017, 11, 9143-9150.	14.6	164
11	Carrier-Type Modulation and Mobility Improvement of Thin MoTe ₂ . Advanced Materials, 2017, 29, 1606433.	21.0	158
12	Colossal grain growth yields single-crystal metal foils by contact-free annealing. Science, 2018, 362, 1021-1025.	12.6	158
13	Large-area single-crystal AB-bilayer and ABA-trilayer graphene grown on a Cu/Ni(111) foil. Nature Nanotechnology, 2020, 15, 289-295.	31.5	141
14	Highly Oriented Monolayer Graphene Grown on a Cu/Ni(111) Alloy Foil. ACS Nano, 2018, 12, 6117-6127.	14.6	132
15	Patterning metal contacts on monolayer MoS ₂ with vanishing Schottky barriers using thermal nanolithography. Nature Electronics, 2019, 2, 17-25.	26.0	113
16	Electrical characterization of 2D materials-based field-effect transistors. 2D Materials, 2021, 8, 012002.	4.4	111
17	A Fermi-Level-Pinning-Free 1D Electrical Contact at the Intrinsic 2D MoS ₂ -Metal Junction. Advanced Materials, 2019, 31, e1808231.	21.0	108
18	A new mussel-inspired polydopamine phototransistor with high photosensitivity: signal amplification and light-controlled switching properties. Chemical Communications, 2014, 50, 1458-1461.	4.1	107

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19	Schottky-Barrier S/D MOSFETs With High- κ Gate Dielectrics and Metal-Gate Electrode. IEEE Electron Device Letters, 2004, 25, 268-270.	3.9	99
20	Carrier transport at the metal-MoS ₂ interface. Nanoscale, 2015, 7, 9222-9228.	5.6	99
21	Metal-Semiconductor Barrier Modulation for High Photoresponse in Transition Metal Dichalcogenide Field Effect Transistors. Scientific Reports, 2014, 4, 4041.	3.3	99
22	Nonvolatile Flash Memory Device Using Ge Nanocrystals Embedded in HfAlO High- κ Tunneling and Control Oxides: Device Fabrication and Electrical Performance. IEEE Transactions on Electron Devices, 2004, 51, 1840-1848.	3.0	97
23	Controlled Folding of Single Crystal Graphene. Nano Letters, 2017, 17, 1467-1473.	9.1	92
24	Adlayer-Free Large-Area Single Crystal Graphene Grown on a Cu(111) Foil. Advanced Materials, 2019, 31, e1903615.	21.0	89
25	High-performance photocurrent generation from two-dimensional WS ₂ field-effect transistors. Applied Physics Letters, 2014, 104, .	3.3	88
26	Monolayer Molybdenum Disulfide Transistors with Single-Atom-Thick Gates. Nano Letters, 2018, 18, 3807-3813.	9.1	88
27	Crystalline zirconia oxide on silicon as alternative gate dielectrics. Applied Physics Letters, 2001, 78, 1604-1606.	3.3	86
28	Si-Compatible Cleaning Process for Graphene Using Low-Density Inductively Coupled Plasma. ACS Nano, 2012, 6, 4410-4417.	14.6	85
29	Fermi Level Pinning Dependent 2D Semiconductor Devices: Challenges and Prospects. Advanced Materials, 2022, 34, e2108425.	21.0	80
30	Passivated ambipolar black phosphorus transistors. Nanoscale, 2016, 8, 12773-12779.	5.6	77
31	Electrically Driven Reversible Phase Changes in Layered In ₂ Se ₃ Crystalline Film. Advanced Materials, 2017, 29, 1703568.	21.0	77
32	Ultrahigh Photoresponsive Device Based on ReS ₂ /Graphene Heterostructure. Small, 2018, 14, e1802593.	10.0	75
33	Multifunctional van der Waals Broken-Gap Heterojunction. Small, 2019, 15, e1804885.	10.0	71
34	Self-assembly of Ni nanocrystals on HfO ₂ and N-assisted Ni confinement for nonvolatile memory application. Applied Physics Letters, 2005, 86, 013107.	3.3	70
35	Control of Etch Slope during Etching of Pt in Ar/Cl ₂ /O ₂ Plasmas. Japanese Journal of Applied Physics, 1996, 35, 2501-2504.	1.5	65
36	Effects of plasma treatment on surface properties of ultrathin layered MoS ₂ . 2D Materials, 2016, 3, 035002.	4.4	59

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37	Van der Waals Broken-Gap π -n Heterojunction Tunnel Diode Based on Black Phosphorus and Rhenium Disulfide. ACS Applied Materials & Interfaces, 2019, 11, 8266-8275.	8.0	58
38	Investigation of electrical conduction in carbon-doped silicon oxide using a voltage ramp method. Applied Physics Letters, 2003, 83, 524-526.	3.3	57
39	Investigation of etching properties of metal nitride/high-k gate stacks using inductively coupled plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2005, 23, 964-970.	2.1	54
40	Tungsten nanocrystals embedded in high-k materials for memory application. Applied Physics Letters, 2005, 87, 113110.	3.3	53
41	Plasma treatments to improve metal contacts in graphene field effect transistor. Journal of Applied Physics, 2011, 110, .	2.5	53
42	Edge contacts of graphene formed by using a controlled plasma treatment. Nanoscale, 2015, 7, 825-831.	5.6	52
43	Formation of Ge nanocrystals in HfAlO high-k dielectric and application in memory device. Applied Physics Letters, 2004, 84, 5407-5409.	3.3	50
44	Spatial Distribution of Charge Traps in a SONOS-Type Flash Memory Using a High- k Trapping Layer. IEEE Transactions on Electron Devices, 2007, 54, 3317-3324.	3.0	49
45	High Electric Field Carrier Transport and Power Dissipation in Multilayer Black Phosphorus Field Effect Transistor with Dielectric Engineering. Advanced Functional Materials, 2017, 27, 1604025.	14.9	47
46	Electrical Characteristics of Memory Devices With a High- k HfO_2 Trapping Layer and Dual $\text{SiO}_2/\text{Si}_3\text{N}_4$ Tunneling Layer. IEEE Transactions on Electron Devices, 2007, 54, 2699-2705.	3.0	46
47	Investigation of etching properties of HfO based high-Kdielectrics using inductively coupled plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 1552-1558.	2.1	43
48	Impact ionization by hot carriers in a black phosphorus field effect transistor. Nature Communications, 2018, 9, 3414.	12.8	41
49	Gate-Modulated Ultrasensitive Visible and Near-Infrared Photodetection of Oxygen Plasma-Treated WSe_2 Lateral pn-Homojunctions. ACS Applied Materials & Interfaces, 2020, 12, 23261-23271.	8.0	41
50	Resonant tunnelling diodes based on twisted black phosphorus homostructures. Nature Electronics, 2021, 4, 269-276.	26.0	41
51	High carrier mobility in graphene doped using a monolayer of tungsten oxyselenide. Nature Electronics, 2021, 4, 731-739.	26.0	41
52	Self-assembly of Al_2O_3 nanodots on SiO_2 using two-step controlled annealing technique for long retention nonvolatile memories. Applied Physics Letters, 2005, 86, 073114.	3.3	38
53	Dielectric Dispersion and High Field Response of Multilayer Hexagonal Boron Nitride. Advanced Functional Materials, 2018, 28, 1804235.	14.9	38
54	Hybrid energy harvester based on nanopillar solar cells and PVDF nanogenerator. Nanotechnology, 2013, 24, 175402.	2.6	37

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55	Electrical properties of crystalline YSZ films on silicon as alternative gate dielectrics. Semiconductor Science and Technology, 2001, 16, L13-L16.	2.0	35
56	High performance vertical tunneling diodes using graphene/hexagonal boron nitride/graphene hetero-structure. Applied Physics Letters, 2014, 104, 053103.	3.3	35
57	Frequency and Temperature Dependence of the Dielectric Properties of a PCB Substrate for Advanced Packaging Applications. Journal of the Korean Physical Society, 2009, 54, 1096-1099.	0.7	35
58	Self-Terminated Surface Monolayer Oxidation Induced Robust Degenerate Doping in MoTe ₂ for Low Contact Resistance. ACS Applied Materials & Interfaces, 2020, 12, 26586-26592.	8.0	34
59	Low temperature MOSFET technology with Schottky barrier source/drain, high-K gate dielectric and metal gate electrode. Solid-State Electronics, 2004, 48, 1987-1992.	1.4	31
60	Self-screened high performance multi-layer MoS ₂ transistor formed by using a bottom graphene electrode. Nanoscale, 2015, 7, 19273-19281.	5.6	31
61	Organic Dye Graphene Hybrid Structures with Spectral Color Selectivity. Advanced Functional Materials, 2016, 26, 6593-6600.	14.9	31
62	High Electric Field Induced Phase Transition and Electrical Breakdown of MoTe ₂ . Advanced Electronic Materials, 2020, 6, 1900964.	5.1	31
63	The device level modulation of carrier transport in a 2D WSe ₂ field effect transistor via a plasma treatment. Nanoscale, 2019, 11, 17368-17375.	5.6	29
64	Enhancement of memory window in short channel non-volatile memory devices using double layer tungsten nanocrystals. , 0, , .		28
65	Reduction of metal contact resistance of graphene devices via CO ₂ cluster cleaning. Applied Physics Letters, 2014, 104, .	3.3	28
66	Fermi Level Pinning Free High Performance 2D CMOS Inverter Fabricated with Van Der Waals Bottom Contacts. Advanced Electronic Materials, 2021, 7, 2001212.	5.1	28
67	High temperature platinum etching using Ti mask layer. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1999, 17, 2151-2155.	2.1	27
68	Three-dimensional metal gate-high- κ -GOI CMOSFETs on 1-poly-6-metal 0.18- μ m Si devices. IEEE Electron Device Letters, 2005, 26, 118-120.	3.9	27
69	Phase-Engineered Molybdenum Telluride/Black Phosphorus Van der Waals Heterojunctions for Tunable Multivalued Logic. ACS Applied Materials & Interfaces, 2020, 12, 14119-14124.	8.0	27
70	Low-Temperature and Large-Scale Production of a Transition Metal Sulfide Vertical Heterostructure and Its Application for Photodetectors. ACS Applied Materials & Interfaces, 2021, 13, 8710-8717.	8.0	27
71	Formation of SiGe nanocrystals in HfO ₂ using in situ chemical vapor deposition for memory applications. Applied Physics Letters, 2004, 84, 4331-4333.	3.3	26
72	Effect of large work function modulation of MoS ₂ by controllable chlorine doping using a remote plasma. Journal of Materials Chemistry C, 2020, 8, 1846-1851.	5.5	26

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73	High performance WSe ₂ p-MOSFET with intrinsic n-channel based on back-to-back p-n junctions. Applied Physics Letters, 2021, 118, .	3.3	26
74	Ohmic Contact in 2D Semiconductors via the Formation of a Benzyl Viologen Interlayer. Advanced Functional Materials, 2019, 29, 1807338.	14.9	24
75	Control of the Schottky Barrier and Contact Resistance at Metal/WSe ₂ Interfaces by Polymeric Doping. Advanced Electronic Materials, 2020, 6, 2000616.	5.1	24
76	Damage-Free Atomic Layer Etch of WSe ₂ : A Platform for Fabricating Clean Two-Dimensional Devices. ACS Applied Materials & Interfaces, 2021, 13, 1930-1942.	8.0	24
77	Investigation of in situ trench etching process and Bosch process for fabricating high-aspect-ratio beams for microelectromechanical systems. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 1878.	1.6	23
78	Unraveling Oxygen Transfer at the Graphene Oxide/ZnO Nanorod Interface. Journal of Physical Chemistry C, 2014, 118, 17638-17642.	3.1	23
79	Identifying the Transition Order in an Artificial Ferroelectric van der Waals Heterostructure. Nano Letters, 2022, 22, 1265-1269.	9.1	23
80	Integral control for synchronization of complex dynamical networks with unknown non-identical nodes. Applied Mathematics and Computation, 2013, 224, 140-149.	2.2	21
81	Kinetics of particle formation in the sputtering and reactive ion etching of silicon. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1992, 10, 1041-1047.	2.1	20
82	Plasma Etching for Sub-45-nm TaN Metal Gates on High-k Dielectrics. IEEE Transactions on Semiconductor Manufacturing, 2007, 20, 143-149.	1.7	20
83	Charge Density Depinning in Defective MoTe ₂ Transistor by Oxygen Intercalation. Advanced Functional Materials, 2020, 30, 2004880.	14.9	20
84	3D GOI CMOSFETs with novel IrO ₂ (Hf) dual gates and high-K dielectric on 1P6M-0.18 μ m-CMOS. , 0, , .		19
85	Lanthanide and Ir-based dual metal-gate/HfAlON CMOS with large work-function difference. , 0, , .		19
86	Edge Rich Ultrathin Layered MoS ₂ Nanostructures for Superior Visible Light Photocatalytic Activity. Langmuir, 2022, 38, 1578-1588.	3.5	19
87	Effects of Conductivity of Polysilicon on Profile Distortion. Japanese Journal of Applied Physics, 1996, 35, 2440-2444.	1.5	18
88	Growth of plasma-generated particles and behavior of particle clouds during sputtering of silicon and silicon dioxide. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1993, 11, 1258-1263.	2.1	17
89	Effects of Annealing and Ar Ion Bombardment on the Removal of HfO ₂ Gate Dielectric. Electrochemical and Solid-State Letters, 2004, 7, F18.	2.2	16
90	Formation of dual-phase HfO ₂ -HfSi _{1-x} O ₂ dielectric and its application in memory devices. Journal of Applied Physics, 2005, 98, 013536.	2.5	16

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91	Optoelectronic Performance of Radial-Junction Si Nanopillar and Nanohole Solar Cells. IEEE Transactions on Electron Devices, 2012, 59, 2368-2374.	3.0	16
92	Kinetics of particle generation in sputtering and reactive ion etching plasmas. Applied Physics Letters, 1992, 60, 1073-1075.	3.3	15
93	A novel program-erasable high- κ AlN-Si MIS capacitor. IEEE Electron Device Letters, 2005, 26, 148-150.	3.9	15
94	Drive-Current Enhancement in FinFETs Using Gate-Induced Stress. IEEE Electron Device Letters, 2006, 27, 769-771.	3.9	15
95	Partial Crystallization of HfO_2 for Two-Bit/Four-Level SONOS-Type Flash Memory. IEEE Transactions on Electron Devices, 2007, 54, 3177-3185.	3.0	15
96	Homogeneous molybdenum disulfide tunnel diode formed via chemical doping. Applied Physics Letters, 2018, 112, .	3.3	15
97	Self-assembled tungsten nanocrystals in high- k dielectric for nonvolatile memory application. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 2278.	1.6	14
98	Low noise RF MOSFETs on flexible plastic substrates. IEEE Electron Device Letters, 2005, 26, 489-491.	3.9	14
99	Energy Dissipation in Black Phosphorus Heterostructured Devices. Advanced Materials Interfaces, 2019, 6, 1801528.	3.7	14
100	Chemical Dopant-Free Doping by Annealing and Electron Beam Irradiation on 2D Materials. Advanced Electronic Materials, 2021, 7, 2100449.	5.1	14
101	Study of leakage mechanisms of the copper/Black Diamond C damascene process. Thin Solid Films, 2004, 462-463, 330-333.	1.8	13
102	Hot-Electron Capture for CHEI Programming in SONOS-Type Flash Memory Using High- k Trapping Layer. IEEE Transactions on Electron Devices, 2008, 55, 1502-1510.	3.0	13
103	Metallic contact induced van der Waals gap in a MoS_2 FET. Nanoscale, 2019, 11, 18246-18254.	5.6	13
104	Traps at the hBN/WSe_2 interface and their impact on polarity transition in WSe_2 . 2D Materials, 2021, 8, 035027.	4.4	13
105	Recent Progress in 1D Contacts for 2D-Material-Based Devices. Advanced Materials, 2022, 34, e2202408.	21.0	13
106	Fast erasing and highly reliable MONOS type memory with HfO_2 high- k trapping layer and $\text{Si}_3\text{N}_4/\text{SiO}_2$ tunneling stack. , 2006, , .		12
107	Investigation of Wet Etching Properties and Annealing Effects of Hf-Based High- k Materials. Journal of the Electrochemical Society, 2006, 153, C483.	2.9	12
108	Enhancement of light absorption using high- k dielectric in localized surface plasmon resonance for silicon-based thin film solar cells. Journal of Applied Physics, 2011, 109, 093516.	2.5	12

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109	Localized Surface Plasmon Resonances by Ag Nanoparticles on SiN for Solar Cell Application. Journal of the Korean Physical Society, 2010, 56, 1488-1491.	0.7	12
110	Effect of Porosity on Electrical Stability of Hydrocarbon Polymeric Low- k Dielectric. IEEE Transactions on Electron Devices, 2005, 52, 2333-2336.	3.0	11
111	Rapid thermal oxidation of Ge-rich Si _{1-x} Ge _x heterolayers. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 84-90.	2.1	11
112	Effects of SiO ₂ /Si ₃ N ₄ hard masks on etching properties of metal gates. Journal of Vacuum Science & Technology B, 2006, 24, 2689.	1.3	11
113	Endurance Reliability of Multilevel-Cell Flash Memory Using a ZrO_2/Si_3N_4 Dual Charge Storage Layer. IEEE Transactions on Electron Devices. 2008, 55, 2361-2369.	3.0	11
114	Formation of polycrystalline silicon germanium/HfO ₂ gate stack structure using inductively coupled plasma etching. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2003, 21, 1210-1217.	2.1	10
115	Effects of Volatility of Etch By-products on Surface Roughness During Etching of Metal Gates in Cl ₂ . Journal of the Electrochemical Society, 2008, 155, H6.	2.9	10
116	Self-Assembled Wire Arrays and ITO Contacts for Silicon Nanowire Solar Cell Applications. Chinese Physics Letters, 2011, 28, 035202.	3.3	10
117	Directly Probing Effective-Mass Anisotropy of Two-Dimensional $ReSe_2$ in Schottky Tunnel Transistors. Physical Review Applied, 2020, 13, .	3.8	10
118	Analytical measurements of contact resistivity in two-dimensional WSe ₂ field-effect transistors. 2D Materials, 2021, 8, 045019.	4.4	9
119	Process-induced particle formation in the sputtering and reactive ion etching of silicon and silicon dioxide. Plasma Sources Science and Technology, 1994, 3, 273-277.	3.1	8
120	Reliability improvement using buried capping layer in advanced interconnects. , 0, , .		8
121	Sub-30 nm Strained p-Channel Fin-Type Field-Effect Transistors with Condensed SiGe Source/Drain Stressors. Japanese Journal of Applied Physics, 2007, 46, 2058-2061.	1.5	8
122	Deep level transient spectroscopy on charge traps in high-k ZrO ₂ . Thin Solid Films, 2010, 518, 6382-6384.	1.8	8
123	Temperature of a Semiconducting Substrate Exposed to an Inductively Coupled Plasma. Journal of the Korean Physical Society, 2011, 59, 262-270.	0.7	8
124	Metal-Insulator Transition Driven by Traps in 2D WSe ₂ Field-Effect Transistor. Advanced Electronic Materials, 2022, 8, .	5.1	8
125	Anisotropic etching characteristics of platinum electrode for ferroelectric capacitor. IEEE Transactions on Electron Devices, 1999, 46, 984-992.	3.0	7
126	Roles of F and O Radicals and Positive Ions in a SF ₆ /O ₂ Plasma in Forming Deep Via Structures. Journal of the Korean Physical Society, 2009, 54, 1774-1778.	0.7	7

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127	Controlling Carrier Transport in Vertical MoTe ₂ /MoS ₂ van der Waals Heterostructures. ACS Applied Materials & Interfaces, 2021, 13, 54294-54300.	8.0	7
128	Enhancement of adhesion strength of Cu layer on single and multi-layer dielectric film stack in Cu/low k multi-level interconnects. Microelectronic Engineering, 2004, 75, 183-193.	2.4	6
129	Effects of N ₂ , O ₂ , and Ar plasma treatments on the removal of crystallized HfO ₂ film. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 133-140.	2.1	6
130	SELF-ASSEMBLY OF Si NANOSTRUCTURES IN SF ₆ /O ₂ PLASMA. Nano, 2008, 03, 169-173.	1.0	6
131	Pulse-agitated self-convergent programming for 4-bit per cell dual charge storage layer flash memory. Solid-State Electronics, 2010, 54, 14-17.	1.4	6
132	Multi-level cell storage with a modulated current method for phase-change memory using Ge-doped SbTe. Current Applied Physics, 2011, 11, e79-e81.	2.4	6
133	High carrier mobility in Si-MOSFETs with a hexagonal boron nitride buffer layer. Solid State Communications, 2015, 209-210, 1-4.	1.9	6
134	Contact Resistivity in Edge-Contacted Graphene Field Effect Transistors. Advanced Electronic Materials, 2022, 8, .	5.1	6
135	In situ trench etching and releasing technique of high aspect ratio beams using magnetically enhanced reactive ion etching. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 154.	1.6	5
136	Modified Potential Well Formed by $\text{Si/SiO}_2/\text{TiN/TiO}_2/\text{SiO}_2/\text{TaN}$ for Flash Memory Application. IEEE Transactions on Electron Devices, 2010, 57, 2794-2800.	3.0	5
137	Anomalously persistent p-type behavior of WSe ₂ field-effect transistors by oxidized edge-induced Fermi-level pinning. Journal of Materials Chemistry C, 2022, 10, 846-853.	5.5	5
138	Ultrahigh Anisotropic Transport Properties of Black Phosphorus Field Effect Transistors Realized by Edge Contact. Advanced Electronic Materials, 2022, 8, .	5.1	5
139	Reactive Ion Etching of Copper with SiCl ₄ and CCl ₂ F ₂ . Materials Research Society Symposia Proceedings, 1990, 201, 129.	0.1	4
140	Mechanism of particle formation in the sputtering and reactive ion etching of Si and SiO ₂ . Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1994, 12, 2758.	1.6	4
141	Effect of electric field on chemical bonds of carbon-doped silicon oxide as evidenced by in situ Fourier transform infrared spectroscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 433.	1.6	4
142	Formation of PtSi Schottky barrier MOSFETs using plasma etching. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	2.1	4
143	Effects of Nanostructures Formed by Plasma Etching on the Reflectance of Solar Cells. Journal of the Korean Physical Society, 2009, 54, 1016-1020.	0.7	4
144	Simulation of trapping properties of high ϵ_r material as the charge storage layer for flash memory application. Thin Solid Films, 2006, 504, 209-212.	1.8	3

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145	Novel ZrO_2/Si_3N_4 Dual Charge Storage Layer to Form Step-Up Potential Wells for Highly Reliable Multi-Level Cell Application. , 2007, , .		3
146	V_{th} Control by Complementary Hot-Carrier Injection for SONOS Multi-Level Cell Flash Memory. IEEE Transactions on Electron Devices, 2009, 56, 3027-3032.	3.0	3
147	Estimation of Trapped Charge Density in SONOS Flash Memory Using a Parallel Capacitor Model. IEEE Transactions on Electron Devices, 2011, 58, 3254-3259.	3.0	3
148	Modified write-and-verify scheme for improving the endurance of multi-level cell phase-change memory using Ge-doped SbTe. Solid-State Electronics, 2012, 76, 67-70.	1.4	3
149	Chemical analysis of etching residues in metal gate stack for CMOS process. Studies in Surface Science and Catalysis, 2006, 159, 365-368.	1.5	2
150	Low energy N_2 ion bombardment for removal of $(HfO_2)_x(SiON)_{1-x}$ in dilute HF. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2007, 25, 1056-1061.	2.1	2
151	Second-Bit-Effect-Free Multibit-Cell Flash Memory Using Si_3N_4/ZrO_2 Split Charge Trapping Layer. IEEE Transactions on Electron Devices, 2009, 56, 1966-1973.	3.0	2
152	Application of the Black Silicon Phenomenon to Forming High-Aspect-Ratio Deep Vias. Journal of the Korean Physical Society, 2009, 54, 616-620.	0.7	2
153	Comprehensive Modulation of Conductance Anisotropy in Low-Symmetry ReS_2 Transistors. Physical Review Applied, 2022, 17, .	3.8	2
154	Heterogeneous Particle Formation during Low Pressure Etching of Silicon Dioxide. Japanese Journal of Applied Physics, 1997, 36, 4971-4975.	1.5	1
155	Chemical Vapor Deposition of Germanium Nanocrystals on Hafnium Oxide for Non-Volatile Memory Applications. Materials Research Society Symposia Proceedings, 2004, 830, 299.	0.1	1
156	Direct trim etching process of Si/SiO ₂ gate stacks using 193 nm ArF patterns. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 1500-1505.	2.1	1
157	Impact of buried capping layer on electrical stability of advanced interconnects. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1499.	1.6	1
158	Impact of buried capping layer on TDDDB physics of advanced interconnects. , 0, , .		1
159	Integrated process of photoresist trimming and dielectric hard mask etching for sub-50 nm gate patterning. Thin Solid Films, 2006, 504, 117-120.	1.8	1
160	Novel HFAIO charge trapping layer in SONOS type flash memory for multi-bit per cell operation. , 2006, , .		1
161	Improvement of Multiple-Level Cell Endurance of NAND Flash Memories Using HfO ₂ /ZrO ₂ Charge Storage Layer. ECS Transactions, 2007, 11, 519-528.	0.5	1
162	A time-dependent technique for carrier recombination and generation lifetime measurement in SOI MOSFET. Solid-State Electronics, 2008, 52, 1773-1777.	1.4	1

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163	High-Speed Multilevel nand Flash Memory With Tight V_{th} Distribution Using an Engineered Potential Well and Forward-Bias Adjusted Programming. IEEE Transactions on Electron Devices, 2011, 58, 3321-3328.	3.0	1
164	High photocurrent and quantum efficiency of graphene photodetector using layer-by-layer stack structure and trap assistance. , 2012, , .		1
165	Removal of Plasma-Induced Physical Damage Formed in Nanoscale Three-Dimensional FinFETs. Nano, 2017, 12, 1750099.	1.0	1
166	Hydrogen-Induced Damage During the Plasma Etching Process. Nano, 2017, 12, 1750112.	1.0	1
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